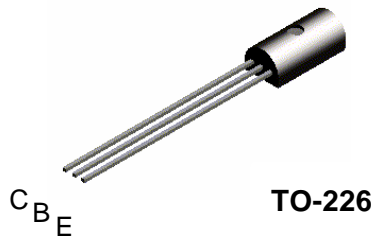


TN6725A



TO-226

NPN Darlington Transistor

This device is designed for applications requiring extremely high current gain at collector currents to 1A. Sourced from Process 05. See MPSA14 for characteristics.

Absolute Maximum Ratings* T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CES}	Collector-Emitter Voltage	50	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	12	V
I _C	Collector Current - Continuous	1.2	A
T _{J, Tstg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150°C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics T_A = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		TN6725A	
P _D	Total Device Dissipation Derate above 25°C	1	W
		8	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	50	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	125	°C/W

NPN Darlington Transistor

(continued)

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
BV_{CES}	Collector-Emitter Breakdown Voltage	$I_C = 1 \text{ mA}$	50		V
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu\text{A}$	60		V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}$	12		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 40 \text{ V}$		100	nA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 10 \text{ V}$		100	nA
ON CHARACTERISTICS*					
h_{FE}	DC Current Gain	$I_C = 200 \text{ mA}, V_{CE} = 5 \text{ V}$ $I_C = 500 \text{ mA}, V_{CE} = 5 \text{ V}$ $I_C = 1 \text{ A}, V_{CE} = 5 \text{ V}$	25,000 15,000 4000	40,000	-
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 200 \text{ mA}, I_B = 2 \text{ mA}$ $I_C = 1 \text{ A}, I_B = 2 \text{ mA}$		1.0 1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 1 \text{ A}, I_B = 2 \text{ mA}$		2	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 1 \text{ A}, V_{CE} = 5.0 \text{ V}$		2	V
SMALL SIGNAL CHARACTERISTICS					
C_{cb}	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1\text{MHz}$		10	pF
h_{fe}	Small Signal Current Gain	$I_C = 200 \text{ mA}, V_{CE} = 5 \text{ V}, f=100\text{MHz}$	1	10	-

*Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 1.0\%$